

HEF4952B

Dual 3-channel analog multiplexer/demultiplexer with supplementary switches

Rev. 03 — 16 December 2009

Product data sheet

1. General description

The HEF4952B is a dual 3-channel analog multiplexer/demultiplexer with supplementary switches and common select logic. Each switch features three independent inputs/outputs (pins nY0, nY1 and nY2) an input/output nY3 that can be connected to nY2 or V_{SS} and an input/output (nZ) common to nY0, nY1 and nY2. Three digital select inputs (S1, S2 and S3) are common to both switches. Inputs include clamp diodes, this enables the use of current limiting resistors to interface inputs in excess of V_{DD} .

V_{SS} and V_{DD} are the digital control supply pins.

The HEF4952B is suitable for use over the full industrial ($-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$) temperature range.

2. Features

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Schmitt-trigger action at control inputs
- Small signal switch
- Standardized symmetrical output characteristics
- Operates across the full industrial temperature range $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$
- Complies with JEDEC standard JESD 13-B

3. Applications

- Industrial
- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating

4. Ordering information

Table 1. Ordering information

All types operate from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$.

| Type number | Package | | Version |
|-------------|---------|--|----------|
| | Name | Description | |
| HEF4952BT | SO16 | plastic small outline package; 16 leads; body width 3.9 mm | SOT109-1 |

5. Functional diagram

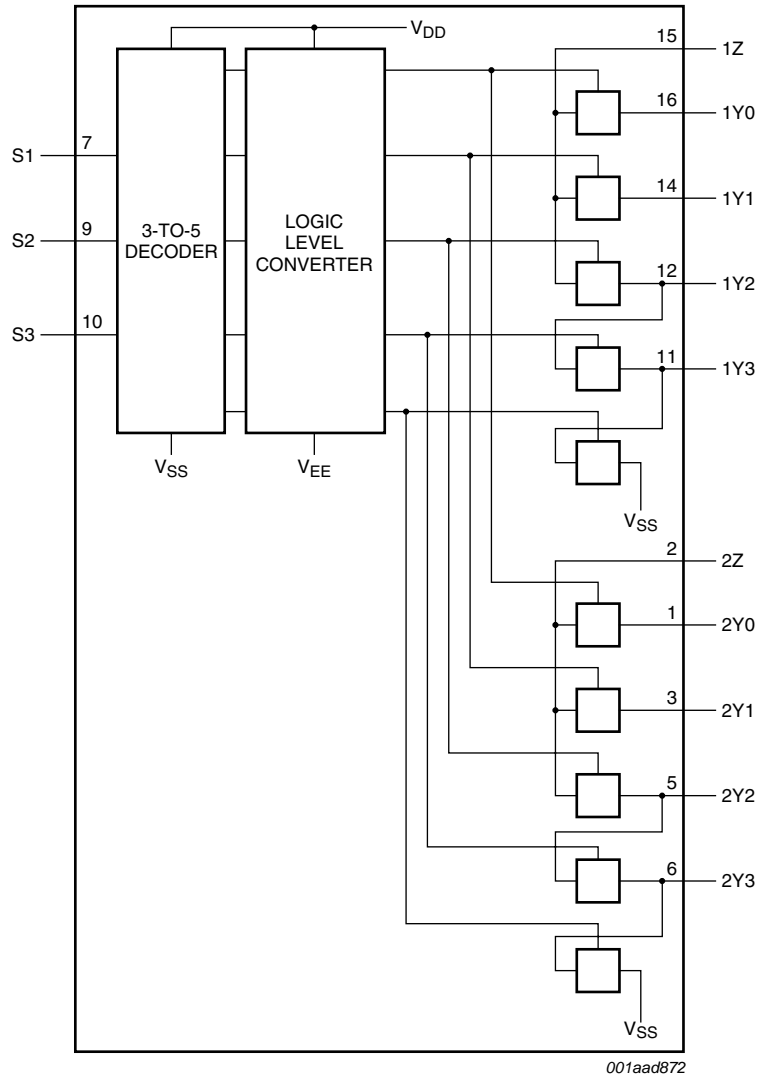


Fig 1. Functional diagram

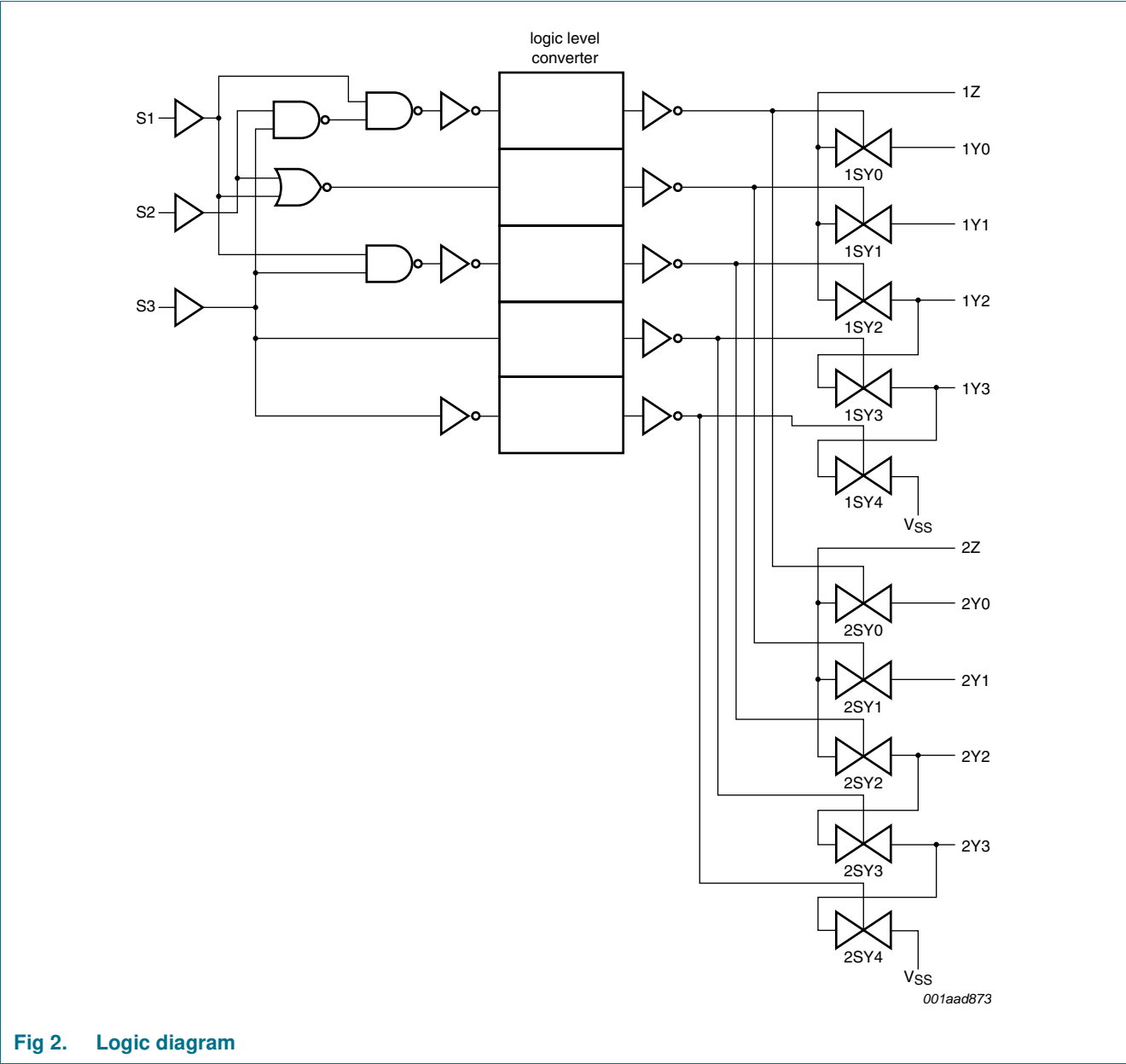


Fig 2. Logic diagram

6. Pinning information

6.1 Pinning

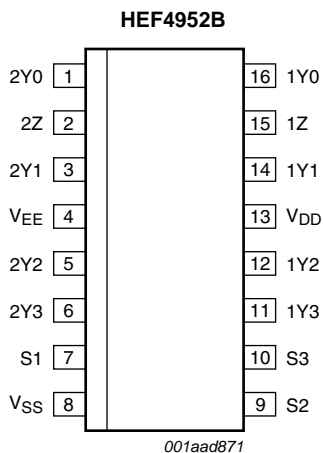


Fig 3. Pin configuration

6.2 Pin description

Table 2. Pin description

| Symbol | Pin | Description |
|--|----------------------------|-----------------------------|
| V _{EE} | 4 | supply voltage |
| V _{SS} | 8 | ground supply voltage |
| S1, S2, S3 | 7, 9, 10 | select input |
| 1Y0, 1Y1, 1Y2, 1Y3, 2Y0, 2Y1, 2Y2, 2Y3 | 16, 14, 12, 11, 1, 3, 5, 6 | independent input or output |
| 1Z, 2Z | 15, 2 | common output or input |
| V _{DD} | 13 | supply voltage |

7. Functional description

7.1 Function table

Table 3. Function table

| Input | | | Switch | | | | |
|-------|----|----|-----------|-----------|-----------|------------|------------------------|
| S3 | S2 | S1 | nSY0 | nSY1 | nSY2 | nSY3 | nSY4 |
| L | L | L | open | nY1 to nZ | open | open | nY3 to V _{SS} |
| L | L | H | nY0 to nZ | open | open | open | nY3 to V _{SS} |
| L | H | L | open | open | nY2 to nZ | open | nY3 to V _{SS} |
| L | H | H | nY0 to nZ | open | nY2 to nZ | open | nY3 to V _{SS} |
| H | L | L | open | nY1 to nZ | open | nY2 to nY3 | open |
| H | L | H | nY0 to nZ | open | open | nY2 to nY3 | open |
| H | H | L | open | open | nY2 to nZ | nY2 to nY3 | open |
| H | H | H | open | open | open | nY2 to nY3 | open |

- [1] H = HIGH voltage level;
L = LOW voltage level.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to V_{SS} = 0 V (ground).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|---------|-----------------------|------|
| V _{DD} | supply voltage | | -0.5 | +18 | V |
| V _{EE} | supply voltage | referenced to V _{DD} | [1] -18 | +0.5 | V |
| I _{IK} | input clamping current | pins Sn; V _I < -0.5 V or V _I > V _{DD} + 0.5 V | - | ±10 | mA |
| V _I | input voltage | | -0.5 | V _{DD} + 0.5 | V |
| I _{I/O} | input/output current | | - | ±10 | mA |
| I _{DD} | supply current | | - | 50 | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| T _{amb} | ambient temperature | | -40 | +85 | °C |
| P _{tot} | total power dissipation | T _{amb} = -40 °C to +85 °C | [2] - | 500 | mW |
| P | power dissipation | per output | - | 100 | mW |

- [1] To avoid drawing V_{DD} current out of terminal Z, when switch current flows into terminals Y, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no V_{DD} current will flow out of terminals Y, and in this case there is no limit for the voltage drop across the switch, but the voltages at Y and Z may not exceed V_{DD} or V_{EE}.

- [2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------|---------------------|------------------------------|-----|-----|----------|------|
| V_{DD} | supply voltage | see Figure 4 | 5 | - | 15 | V |
| V_{EE} | supply voltage | see Figure 4 | -15 | - | 0 | V |
| V_I | input voltage | | 0 | - | V_{DD} | V |
| T_{amb} | ambient temperature | in free air | -40 | - | +85 | °C |

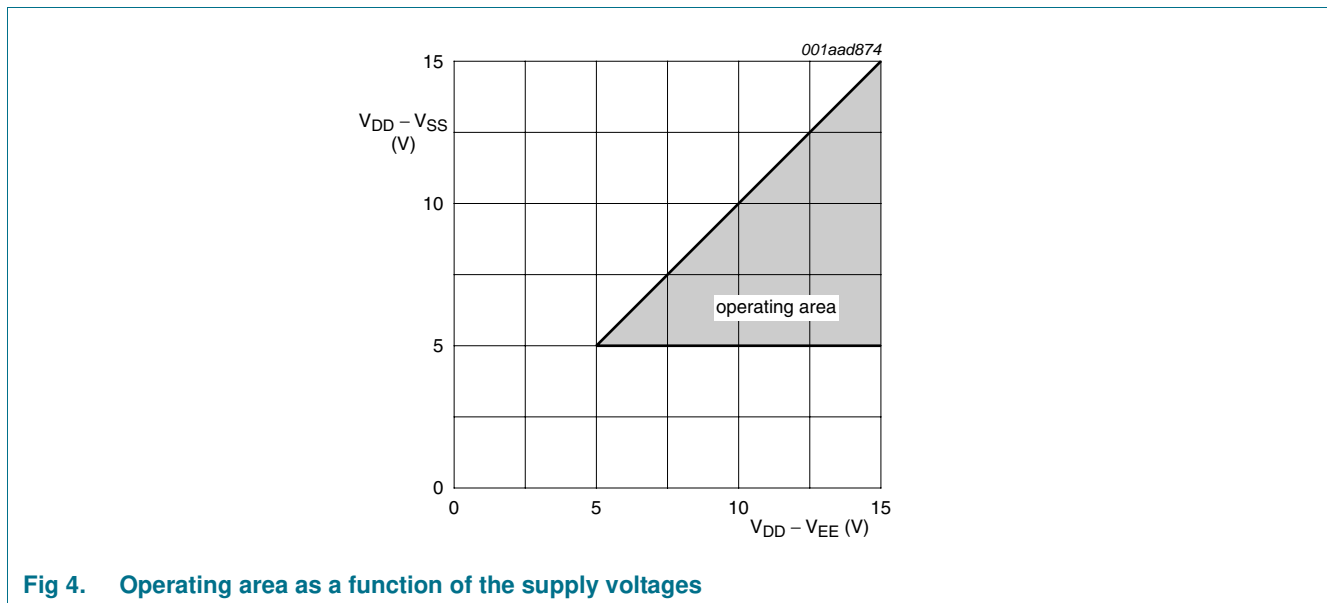


Fig 4. Operating area as a function of the supply voltages

10. Static characteristics

Table 6. Static characteristics

$V_{SS} = V_{EE} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

| Symbol | Parameter | Conditions | V_{DD} | $T_{amb} = -40\text{ °C}$ | | $T_{amb} = 25\text{ °C}$ | | $T_{amb} = 85\text{ °C}$ | | Unit |
|--------------|---------------------------|---|----------|---------------------------|------|--------------------------|------|--------------------------|------|------|
| | | | | Min | Max | Min | Max | Min | Max | |
| I_I | input leakage current | | 15 V | - | ±0.3 | - | ±0.3 | - | ±1.0 | µA |
| $I_{S(OFF)}$ | OFF-state leakage current | Y port; per channel; see Figure 5 | 15 V | - | - | - | 200 | - | - | nA |
| I_{DD} | supply current | $I_O = 0\text{ A}$ | 5 V | - | 20 | - | 20 | - | 150 | µA |
| | | | 10 V | - | 40 | - | 40 | - | 300 | µA |
| | | | 15 V | - | 80 | - | 80 | - | 600 | µA |
| C_I | input capacitance | Sn inputs | - | - | - | 7.5 | - | - | pF | |

10.1 Test circuits

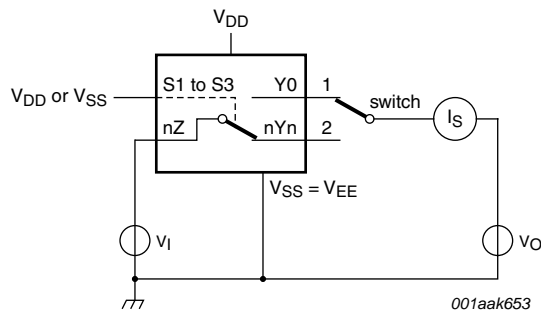


Fig 5. Test circuit for measuring OFF-state leakage current nYn port

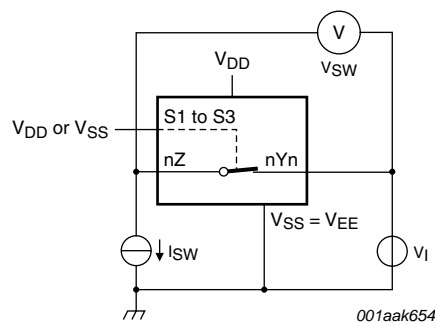
10.2 On resistance

Table 7. ON resistance

$T_{amb} = 25\text{ }^{\circ}\text{C}$; $I_{SW} = 200\text{ }\mu\text{A}$; $V_{SS} = V_{EE} = 0\text{ V}$.

| Symbol | Parameter | Conditions | $V_{DD} - V_{EE}$ | Typ | Max | Unit |
|-----------------|---|--|-------------------|-----|-----|----------|
| R_{ON} | ON resistance | $V_I = 0\text{ V}$; see Figure 6 and Figure 7 | 10 V | 45 | 150 | Ω |
| | | $V_I = 2.5\text{ V}$; see Figure 6 and Figure 7 | 10 V | 65 | 365 | Ω |
| | | $V_I = 5.0\text{ V}$; see Figure 6 and Figure 7 | 10 V | 110 | 360 | Ω |
| ΔR_{ON} | ON resistance mismatch between channels | $V_I = 2.5\text{ V}$; see Figure 6 | 10 V | 10 | - | Ω |

10.2.1 On resistance waveform and test circuit



$$R_{ON} = V_{SW} / I_{SW}$$

Fig 6. Test circuit for measuring R_{ON}

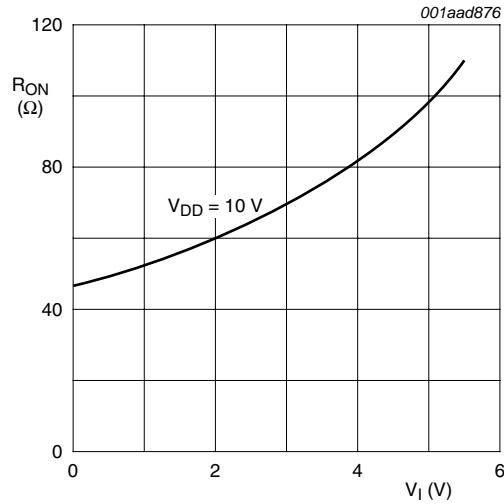


Fig 7. Typical RON as a function of input voltage

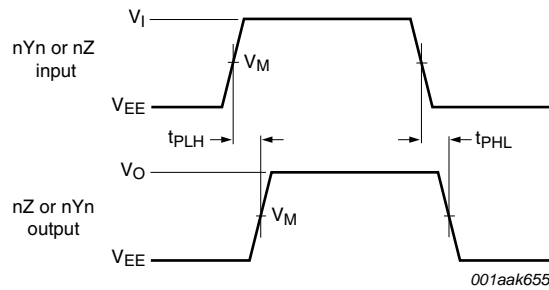
11. Dynamic characteristics

Table 8. Dynamic characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$; $V_{SS} = V_{EE} = 0\text{ V}$; for test circuit see [Figure 10](#).

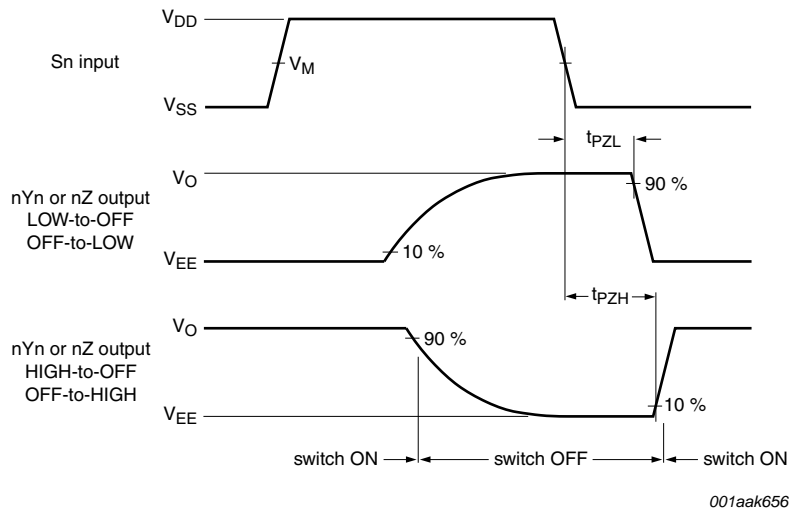
| Symbol | Parameter | Conditions | V _{DD} | Typ | Max | Unit |
|------------------|-------------------------------------|--|-----------------|-----|-----|------|
| t _{PHL} | HIGH to LOW propagation delay | nYn, nZ to nZ, nYn; V _I = 1.0 V; see Figure 8 | 5 V | 5 | - | ns |
| | | | 10 V | 3 | 6 | ns |
| | | | 15 V | 2 | - | ns |
| t _{PLH} | LOW to HIGH propagation delay | nYn, nZ to nZ, nYn; V _I = 1.0 V; see Figure 8 | 5 V | 5 | - | ns |
| | | | 10 V | 3 | 6 | ns |
| | | | 15 V | 2 | - | ns |
| t _{PZL} | OFF-state to LOW propagation delay | Sn to nYn, nZ; V _I = V _{EE} ; see Figure 9 | 5 V | 125 | - | ns |
| | | | 10 V | 50 | 100 | ns |
| | | | 15 V | 35 | - | ns |
| t _{PZH} | OFF-state to HIGH propagation delay | Sn to nYn, nZ; V _I = 1.0 V; see Figure 9 | 5 V | 125 | - | ns |
| | | | 10 V | 50 | 100 | ns |
| | | | 15 V | 35 | - | ns |

11.1 Waveforms and test circuit



Measurement points are given in [Table 9](#).

Fig 8. nYn, nZ to nZ, nYn propagation delays

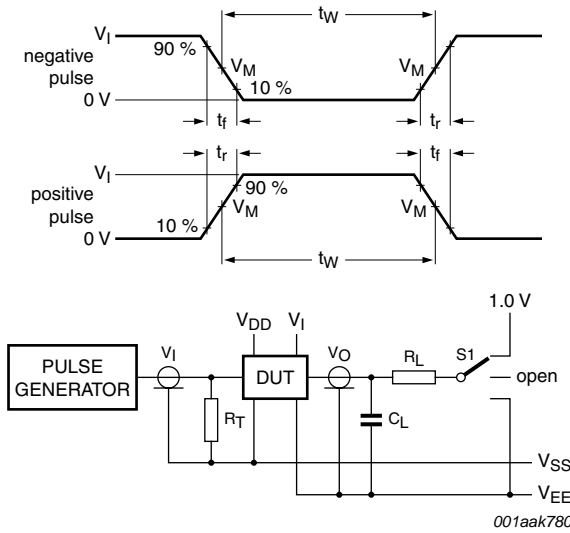


Measurement points are given in [Table 9](#).

Fig 9. Enable and disable times

Table 9. Measurement points

| Supply voltage | Input | Output |
|----------------|-------------|-------------|
| V_{DD} | V_M | V_M |
| 5 V to 15 V | $0.5V_{DD}$ | $0.5V_{DD}$ |



Test data is given in [Table 10](#).

Definitions:

DUT = Device Under Test.

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including test jig and probe.

R_L = Load resistance.

Fig 10. Test circuit for measuring switching times

Table 10. Test data

| Input | | | | Load | | S1 position | | | |
|-----------------------------------|------------------------------------|---------------------------------|--------------------|----------------|----------------|-------------------------------------|------------------|------------------|-----------------|
| nYn, nZ | Sn | t _r , t _f | V _M | C _L | R _L | t _{PHL} , t _{PLH} | t _{PZH} | t _{PZL} | Other |
| V _I or V _{EE} | V _{DD} or V _{SS} | ≤ 20 ns | 0.5V _{DD} | 50 pF | 10 kΩ | V _{EE} | V _{EE} | 1.0 V | V _{EE} |

Table 11. Dynamic power dissipation P_D

P_D can be calculated from the formulas shown; $V_{EE} = V_{SS} = 0 V$; $t_r = t_f \leq 20 ns$; $T_{amb} = 25 °C$.

| Symbol | Parameter | V _{DD} | Typical formula for P _D (μW) | Where: |
|----------------|---------------------------|-----------------|---|--|
| P _D | dynamic power dissipation | 5 V | $P_D = 1300 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ | f_i = input frequency in MHz; |
| | | 10 V | $P_D = 6100 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ | f_o = output frequency in MHz; |
| | | 15 V | $P_D = 15600 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ | C_L = output load capacitance in pF; |
| | | | | V _{DD} = supply voltage in V; |
| | | | | $\Sigma(f_o \times C_L)$ = sum of the outputs. |

11.2 Transfer characteristics

Table 12. Control input characteristics

$V_{SS} = V_{EE} = 0$ V unless otherwise specified.

| Symbol | Parameter | Conditions | T _{amb} = 25 °C | | T _{amb} = -40 °C to +85 °C | | Unit |
|-----------------|----------------------------------|------------------------|--------------------------|------|-------------------------------------|------|------|
| | | | Min | Max | Min | Max | |
| V _{T+} | positive-going threshold voltage | V _{DD} = 5 V | - | 2.90 | - | 3.00 | V |
| | | V _{DD} = 10 V | - | 4.37 | - | 4.50 | V |
| V _{T-} | negative-going threshold voltage | V _{DD} = 5 V | 1.03 | - | 1.00 | - | V |
| | | V _{DD} = 10 V | 2.10 | - | 2.00 | - | V |
| V _H | hysteresis voltage | V _{DD} = 5 V | 0.16 | - | 0.10 | - | V |
| | | V _{DD} = 10 V | 0.11 | - | 0.10 | - | V |

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

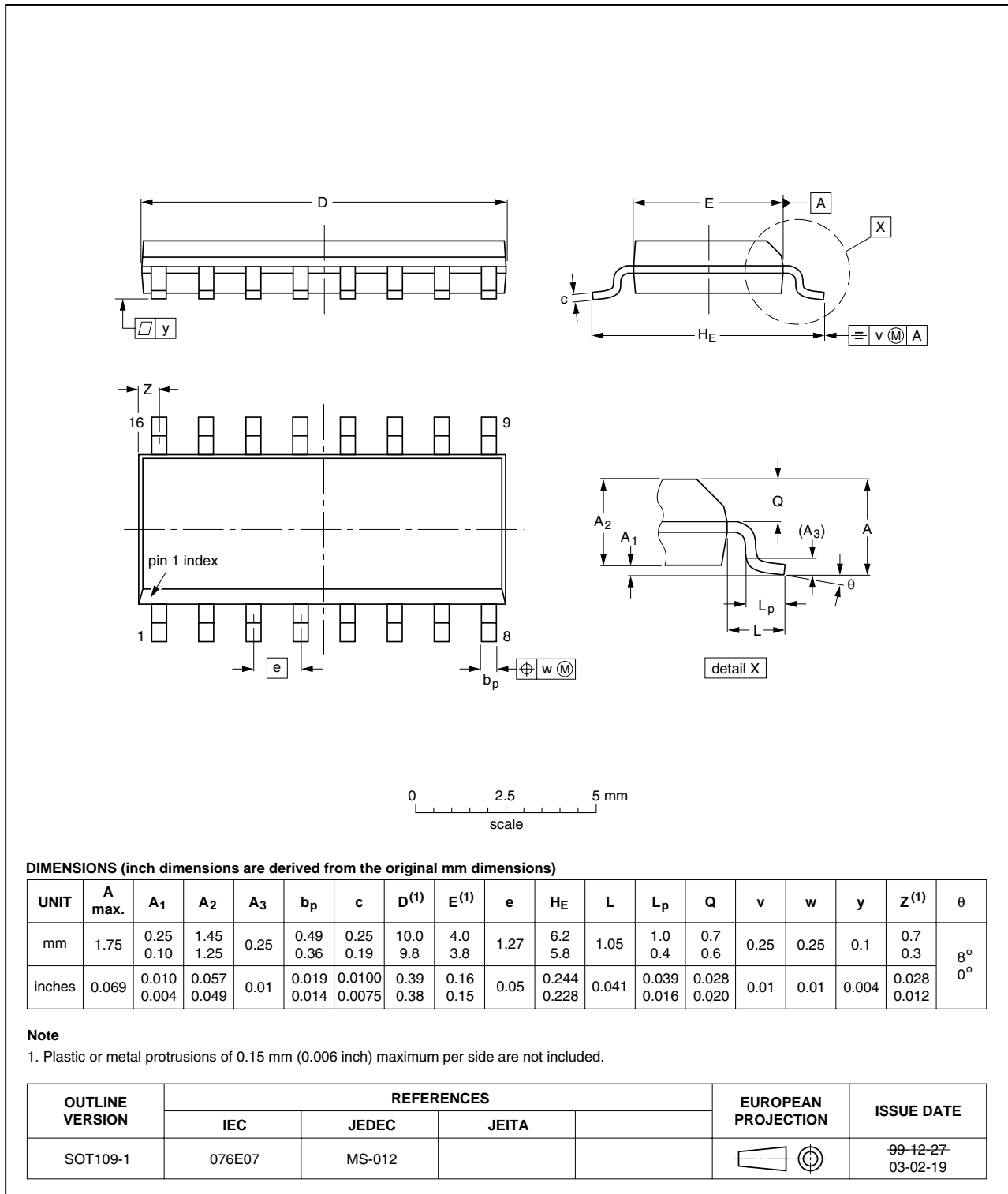


Fig 11. Package outline SOT109-1 (SO16)

13. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--|---------------|------------|
| HEF4952B_3 | 20091216 | Product data sheet | - | HEF4952B_2 |
| Modifications: | | <ul style="list-style-type: none">Title changed from 8-channel analog multiplexer/demultiplexer.Section 1 "General description" modified.Section 8 "Limiting values" I_{IK} conditions updated.Abbreviations section removed. | | |
| HEF4952B_2 | 20091002 | Product data sheet | - | HEF4952B_1 |
| HEF4952B_1 | 20060320 | Product data sheet | - | - |

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|-----------------------------------|-------------------------------|---|
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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